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Q1 Surface and bulk crystallization of amorphous solid water films: 2 Confirmation of "top-down" crystallization

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ABSTRACT

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The crystallization kinetics of nanoscale amorphous solid water (ASW) films are investigated using temperatureprogrammed desorption (TPD) and reflection absorption infrared spectroscopy (RAIRS). TPD measurements are used to probe surface crystallization and RAIRS measurements are used to probe bulk crystallization. Isothermal TPD results show that surface crystallization is independent of the film thickness (from 100 to 1000 ML). Conversely, the RAIRS measurements show that the bulk crystallization time increases linearly with increasing film thickness. These results suggest that nucleation and crystallization begin at the ASW/vacuum interface and then the crystallization growth front propagates linearly into the bulk. This mechanism was confirmed by selective placement of an isotopic layer (5% D₂O in H₂O) at various positions in an ASW (H₂O) film. In this case, the closer the isotopic layer was to the vacuum interface, the earlier the isotopic layer crystallized. These experiments provide direct evidence to confirm that ASW crystallization in vacuum proceeds by a "top-down" crystallization mechanism.

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36 1. Introduction

Amorphous solid water (ASW) is a metastable glassy phase form of 37water that can be created in the laboratory by vapor deposition onto a 38 cold substrate (T < 130 K). The properties of ASW are of interest for a 39 variety of reasons including its use as a model for liquid and 40supercooled liquid water [1–5], its use as a model for studying the 41 properties of amorphous solids, and because it is believed to be the 42 predominant form of water in astrophysical and planetary environ-43 ments [6-8]. The crystallization of ASW films has been studied 44 45 using a variety of methods including temperature-programmed desorption (TPD) [9–15], adsorbate physisorption [16–20], electron 46diffraction [21,22], and infrared techniques [14,15,20,23-25]. Most 47 of these studies either report or assume that ASW crystallization 4849 proceeds via a random bulk nucleation and growth mechanism. However, one study reports that crystallization may start at the 50vacuum interface, although detailed kinetic modeling was required to 5152separate the surface and bulk crystallization rates in the relatively thin film (45 ML) [20,26]. 53

It has been shown previously that inert adsorbates trapped underneath or within ASW films desorb in an episodic release that occurs in concert with ASW crystallization, a phenomenon called the "molecular volcano" [27,28]. The abrupt desorption of gases is due to cracks that form during crystallization of the ASW overlayer. Some

http://dx.doi.org/10.1016/j.susc.2015.12.037 0039-6028/© 2016 Published by Elsevier B.V. more recent work studying the crack formation that accompanies59ASW crystallization in thicker films showed that crack formation begins60at the ASW/vacuum interface [29–31]. In that work, selective placement61of the inert gas layer in the ASW film showed that cracks form near the62top of the film and propagate downward into the film. Given the link63between crystallization and crack formation, these results suggested64that ASW crystallization may also begin at the ASW/vacuum interface65and proceed into the bulk.66

In the present paper, we provide direct evidence that ASW crystalli- 67 zation proceeds via a "top-down" mechanism. This is accomplished 68 by simultaneously monitoring crystallization on the surface and in 69 the bulk as a function of ASW film thickness (100 to 1000 ML). 70 Temperature-programmed desorption (TPD) measurements are used 71 to probe surface crystallization and RAIRS measurements are used to 72 probe bulk crystallization. Our experimental observations are consistent 73 with a two-step model in which nucleation and crystallization begin at the vacuum-ASW and then the crystallization front propagates into the film bulk. 76

2. Material and methods

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The experiments were performed in an ultra-high vacuum system 78 (UHV) with a base pressure of $< 10^{-10}$ Torr that has been described in 79 detail previously [14,32]. Briefly, a 1 cm diameter Pt(111) substrate, 80 cooled by a closed cycle helium cryostat capable of achieving a base 81 temperature of ~25 K, was used as a substrate. The substrate was 82 resistively heated and the temperature was measured by a K-type ther-83 mocouple spot-welded to the back. The temperature was measured 84

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with a precision of better than ± 0.01 K. The absolute temperature was 85 86 calibrated using the desorption of multilayer H₂O TPD and estimated to have an accuracy of ± 2 K. The Pt substrate was cleaned by Ne⁺ ion 87 88 sputtering at 1.5 kV and then annealed at 1100 K in UHV. The Pt substrate was then heated to 1100 K in the presence of decane to 89 form a single layer of graphene on its surface [33]. The ASW films in 90 this experiment were deposited on top of 50 ML of decane to eliminate 9192 (or at least minimize) the potential effects of substrate-induced 93 nucleation. We hypothesize that the long chain hydrocarbon deposited 94at low temperature will not form an extended ordered surface that could act as a crystallization template. Graphene is inert to hydrocarbon 95decomposition (Pt is not) and this provided a clean reproducible surface 96 for growing the ASW/decane films. 97

Water and decane were deposited using a quasi-effusive molecular 98 beam at normal incidence and at ~30 K. Surface crystallization was 99 measured by monitoring the desorption rates of H₂O (m/z = 18) 100 utilizing an Extrel quadrapole mass spectrometer in a line-of-sight 101 configuration. Simultaneous with the desorption measurements, the 102RAIRS spectra were recorded with a Bruker Vertex 70 Fourier transform 103infrared spectrometer where the infrared beam was incident on the 104 sample at an angle of 82 \pm 1°. The infrared spectra were acquired 105with a resolution of 8 cm^{-1} . During a typical isothermal crystallization 106 107 experiment, 100 infrared spectra were acquired in 900 s, and each spectrum was averaged for 64 scans. To clearly measure the ASW 108 crystallization kinetics by infrared spectroscopy, a 5% D₂O in H₂O liquid 109solution was used to create the ASW films. In solution, H-D exchange 110 results in the solution being ~10% HOD. The deposited ASW films have 111 an O-D stretching peak near 2450 cm^{-1} which transforms into a 112 sharp peak at ~2426 cm⁻¹ when crystallized. These peaks (compared 113 to the OH stretch in pure H_2O) are sharper because the O-D stretch of 114 HOD is decoupled from interactions with neighboring OH bonds [34]. 115116 The use of the 5% D_2O in H_2O solution facilitated the analysis of the 117infrared spectra and also allowed for the isotope layer experiments described in Section 3.4. 118

119 **3. Results and discussion**

120 3.1. Surface crystallization of ASW films

The surface crystallization of ASW films in vacuum was determined 121 using isothermal desorption measurements. All ASW films were depos-122123 ited on top of 50 ML of decane. The composite ASW/decane films were deposited at normal incidence and at 30 K. After deposition the films 124 were heated via a linear temperature ramp (1 K/s) to and then held at 125150 K. Fig. 1(a) displays the isothermal TPD spectra for a series of 126 ASW films with thicknesses of 100 (blue curve), 200 (red curve), 500 127128(black curve), and 1000 ML (green curve). The vertical dashed line (t = 0) marks the time when the temperature reaches 150 K. The 129desorption spectra for all four ASW thicknesses are nearly identical 130and have the same desorption rate versus time dependence that has 131 been observed previously [11,15]. This desorption behavior is due to 132133the metastable amorphous phase having a higher free energy than the 134more stable crystalline phase. The higher free energy means that the amorphous phase has a higher vapor pressure than the crystalline 135phase and thus a higher desorption rate. The isothermal spectra in 136Fig. 1(a) show that upon reaching 150 K, the desorption rate is at its 137138 maximum value. Subsequently, the rate decreases in time until about 200 s where the rate plateaus. This is because the initial desorption 139rate is from a film that is nearly all amorphous but as the surface begins 140 to crystallize, the rate decreases until the film's surface is entirely 141 crystalline. 142

The crystallization kinetics can be obtained by analyzing the time dependence of the isothermal desorption rate. In the analysis, the initial desorption rate (\sim 0 s in Fig. 1(a)) is taken to be the desorption rate from a surface that is 100% amorphous, Rate_{ASW}, and the desorption rate in the plateau region (\sim 200 s) is taken to be desorption rate from a surface



Fig. 1. (a) Isothermal TPD spectra for a series of films with ASW thicknesses of 100 (blue curve), 200 (red curve), 500 (black curve), and 1000 ML (green curve). The ASW films (5% D_2 0 in H_2 0 solution) were deposited on top of 50 ML of decane. The composite ASW/decane films were deposited at normal incidence and at 30 K. After deposition the films were heated to and held at 150 K. Time zero (vertical dashed line) marks the time the isothermal temperature is reached. (b) The fraction crystallized versus time, *x*(*t*), obtained from the isothermal TPD spectra in (a).

that is 100% crystalline, Rate_{CI}. The desorption rate in the intermediate 148 region is linear combination of the two desorption rates, 149

$$Rate = Rate_{ASW} \cdot (1 - x(t)) + Rate_{CI} \cdot x(t)$$
(1)

where x(t) is the fraction crystallized at the surface. The fraction 151 crystallized versus time, x(t), is determined using the lever-rule type construction in the equation: 152

$$x(t) = 1 - \frac{\text{Rate}(t) - \text{Rate}_{\text{CI}}}{\text{Rate}_{\text{ASW}} - \text{Rate}_{\text{CI}}}$$
(2)

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Fig. 1(b) displays the x(t) curves obtained from the isothermal TPD spectra in Fig. 1(a) for ASW thicknesses of 100 (blue curve), 200 (red 155 curve), 500 (black curve), and 1000 ML (green curve). The curves for 156 all thicknesses are similar in shape and nearly aligned as is expected 157 since the desorption spectra are nearly identical. The results in Fig. 1 158 confirm that the surface crystallization kinetics of ASW films in vacuum 159 are thickness independent from 100 to 1000 ML. 160

The observed thickness-independent surface crystallization kinetics 161 could be explained by two possible mechanisms. The first mechanism is 162 one where there are random nucleation sites evenly distributed 163 throughout the film. In this case, no matter the film thickness, the 164 surface would crystallize at the same rate given that there is an equal 165 probability of a nearby nucleation site. In this mechanism the bulk 166 crystallization kinetics would also be independent of thickness. The 167 second mechanism is one where there is a preference for nucleation at 168 the ASW surface/vacuum interface. In this case, if the surface is the 169

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